

ST1802HI

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

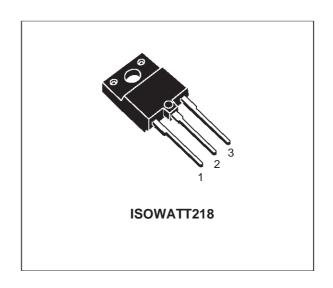
- NEW SERIES, ENHANCHED PERFORMANCE
- FULLY INSULATED PACKAGE FOR EASY MOUNTING
- HIGH VOLTAGE CAPABILITY
- HIGH SWITCHING SPEED
- TIGTHER hfe CONTROL
- IMPROVED RUGGEDNESS

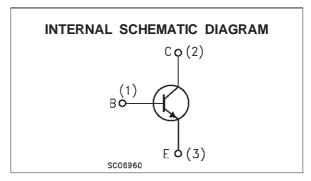
APPLICATIONS:

 HORIZONTAL DEFLECTION FOR COLOR TV

DESCRIPTION

The device is manufactured using Diffused Collector Technology for more stable operation Vs base drive circuit variations resulting in very low worst case dissipation.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage (I _E = 0)	1500	V
Vceo	Collector-Emitter Voltage (I _B = 0)	600	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	7	V
Ic	Collector Current	10	Α
I _{CM}	Collector Peak Current (t _p < 5 ms)	15	Α
lΒ	Base Current	4	Α
P _{tot}	Total Dissipation at T _c = 25 °C	50	W
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

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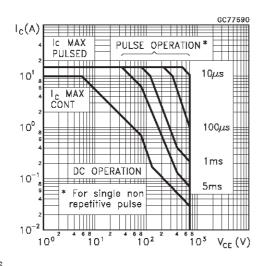
THERMAL DATA

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

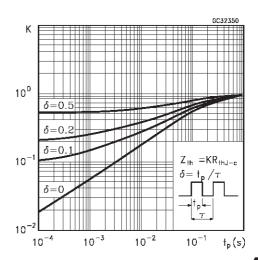
Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 1500 V V _{CE} = 1500 V	T _j = 125 °C			1 2	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 7 V				1	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	L = 25 mH	600			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 4 A I _C = 4 A	$I_B = 0.8 A$ $I_B = 1.2 A$			5 1.5	V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 4.5 A	I _B = 1 A			1.2	V
h _{FE} *	DC Current Gain	I _C = 1 A I _C = 5 A	$V_{CE} = 5 V$ $V_{CE} = 5 V$	4	25	9	
t _s	INDUCTIVE LOAD Storage Time Fall Time	$I_C = 4 A$ $L_B = 5 \mu H$ f = 16 KHz	$I_{Bon(END)} = 1 A$ $V_{BB} = -2.5 V$		5 0.3	6 0.5	μs μs

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

Safe Operating Area

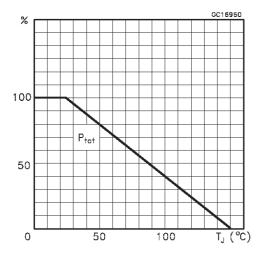


Thermal Impedance

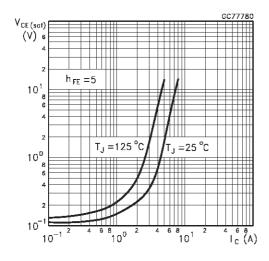


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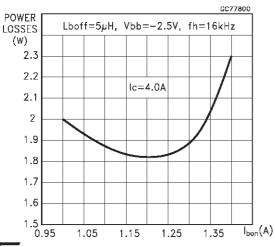
Derating Curve



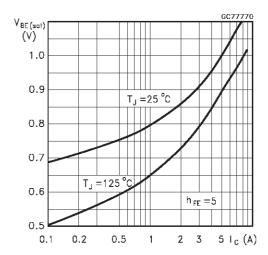
Collector Emitter Saturation Voltage



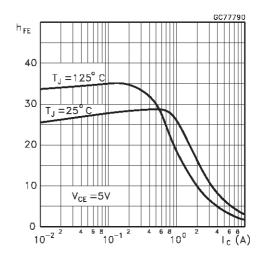
Power Losses At 16 KHz



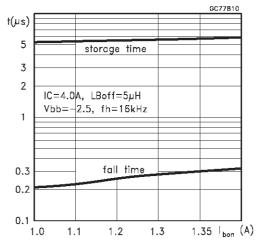
Base Emitter Saturation Voltage



DC Current Gain

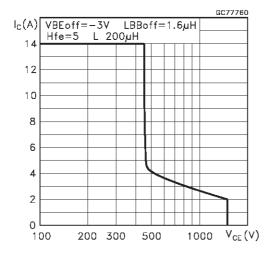


Switching Time Inductive Load

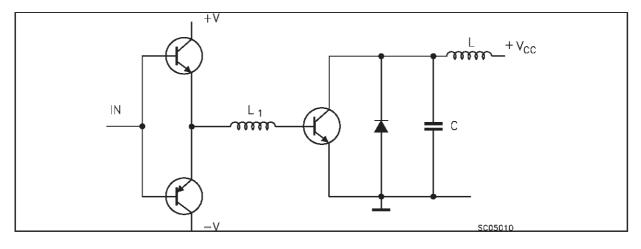


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Reverse Biased SOA



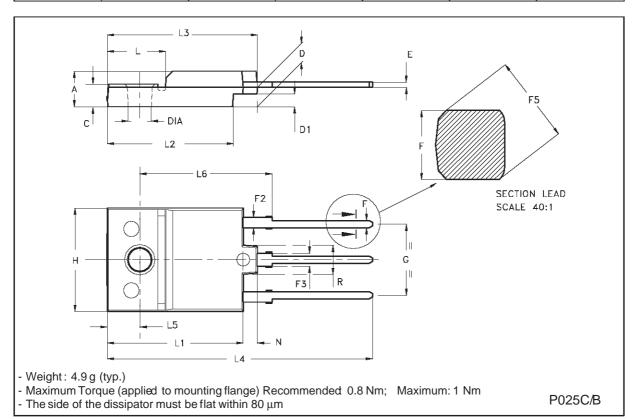
Inductive Load Switching Test Circuits.



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ISOWATT218 NARROW LEADS MECHANICAL DATA

DIM.	mm		inch			
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	5.35		5.65	0.211		0.222
С	3.30		3.80	0.130		0.150
D	2.90		3.10	0.114		0.122
D1	1.88		2.08	0.074		0.082
Е	0.75		0.95	0.030		0.037
F	0.75		0.95	0.030		0.037
F2	1.50		1.70	0.059		0.067
F3	1.90		2.10	0.075		0.083
F5			1.10			0.043
G	10.80		11.20	0.425		0.441
Н	15.80		16.20	0.622		0.638
L		9			0.354	
L1	20.80		21.20	0.819		0.835
L2	19.10		19.90	0.752		0.783
L3	22.80		23.60	0.898		0.929
L4	40.50		42.50	1.594		1.673
L5	4.85		5.25	0.191		0.207
L6	20.25		20.75	0.797		0.817
N	2.1		2.3	0.083		0.091
R		4.6			0.181	
DIA	3.5		3.7	0.138		0.146



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